



PRODUCT/PROCESS CHANGE NOTIFICATION

PCN APG-PTS/14/8309
Dated 05 Feb 2014

**W023 Silicon Line housed in SO-8 : Transfer from
AMK5 to AMK6 and Assy /Final Test from Muar to Shenzhen**

Table 1. Change Implementation Schedule

Forecasted implementation date for change	02-Jun-2014
Forecasted availability date of samples for customer	29-Jan-2014
Forecasted date for STMicroelectronics change Qualification Plan results availability	29-Jan-2014
Estimated date of changed product first shipment	02-Jun-2014

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	see list
Type of change	Waferfab location change
Reason for change	Optimization activity
Description of the change	W023 silicon line housed in SO8 package will be transferred from 5 inchs to 6 inchs in AngMoKio plant (AMK5 ->AMK6) and Assembly / Final Test from ST Muar (Malaysia) to ST Shenzhen (China) plant.
Change Product Identification	Dedicated Finished-Good Codes
Manufacturing Location(s)	

DOCUMENT APPROVAL

Name	Function
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Product Change Notification

W023 Silicon Line housed in SO-8 : Transfer from AMK5 to AMK6 and Assy /Final Test from Muar to Shenzhen

WHAT:

W023 silicon line housed in SO8 package will be transferred from 5 inches to 6 inches in AngMoKio plant (AMK5 -> AMK6) and Assembly / Final Test from ST Muar (Malaysia) to ST Shenzhen (China) plant.

SO8 Assembly Change Matrix from ST Muar to ST Shenzhen

Item	SO-8 Muar	SO-8 Shenzhen
Molding Compound	NITTO MP8000CH4-2A	SUMITOMO EME-G700KC
Die Attach	GLUE ABLEBOND 8601S-25	LOCTITE ABLESTIK 8601S-25
Wires	Au 1 mils	Au 1 mils
Lead-plating	PPF (Ni/Pd/Au)	uPPF (Ni/Pd/Ag-Au)
Lead-plating thic.	40/2/0.2 mils	20/0.5/0.8 mils

WHY:

Optimization Strategy

WHO:

All the Customers that are using the W023 silicon line housed in SO-8 package.

WHEN:

Tentative date of change is June 2014.

Sample available on request

Qualification report included to this PCN (RR005213CT2235).

WHERE:

ST AMK5, AMK6 – ST Muar (Malaysia), ST Shenzhen (China)

L4949ED-E (W023)

BIPOLAR technology transfer from ST AMK5 to ST AMK6

SO8 Assembly transfer from ST Muar to ST Shenzhen

General Information	
Commercial Product	L4949ED-E
Product Line	W023
Silicon process technology	BIP
Package	SO8

Revision history			
Rev.	Date of Release	Author	Changes description
0.1	December 9 th 2013	F. Ceraulo - APG Q&R Catania	Creation

Table of contents		
Section	Pag	Content
1	3	Reliability evaluations overview
1.1	3	Objectives
1.2	3	Results
2	4	Traceability
3	5	Devices characteristics
3.1	5	Generalities
3.2	6	Pins connection
3.3	6	Blocks diagram
3.4	6	Bonding diagram
4	7	Reliability qualification plan and results – Summary table

- 1. Reliability evaluations overview

1.1 Objectives

Aim of this report is to present the results of the reliability evaluations performed on **L4949ED-E** (W023 as ST internal silicon line) in order to qualify both a technology and an assembly processes transfer:

- 1) Diffusion FAB transfer from ST AMK5 Ang Mo Kio (Singapore) 5” wafer fab to ST AMK6 Ang Mo Kio (Singapore) 6” wafer fab;
- 2) SO8 Assembly site transfer from ST Muar (Malaysia) to ST Shenzhen (China).

This product is a monolithic integrated 5V voltage regulator with a very low dropout output and additional functions as power-on reset and input voltage sense for Automotive Application designed in BIPOLAR technology.

The qualification was done according to **AEC_Q100 Rev.G** specification following the path described here below:

Test group as per AEC-Q100 Rev.G		Performed (Y/N)	Comment
A	Accelerated Environment Stress	Y	
B	Accelerated Lifetime Simulation	Y	
C	Package Assembly Integrity	Y	
D	Die Fabrication Reliability	N	Not Applicable for BIPOLAR technology
E	Electrical Verification	Y	
F	Defect Screening	N	To be implemented starting from first production lot
G	Cavity Package Integrity	N	N/A: not for plastic packaged devices

See details per each test group in section 4 of this report.

NOTE: the package oriented tests were done using lots with different assembly configurations both in terms of Bonding Force and Ultra-Sonic Power. 3 lots nominal (NN), 6 lots worst cases (HH: Highest Bonding Force and Highest US Power, LL: Lower Bonding Force and Lower US Power)

1.2 Results

All reliability tests have been completed with positive results neither functional nor parametric rejects were detected at final electrical testing.

Based on the overall positive results we consider the products qualified from a reliability point of view.

- 2. Traceability

Wafer fab information	
Wafer fab manufacturing location	ST AMK6 Ang Mo Kio (Singapore)
Wafer diameter (inches)	6
Silicon process technology	BIP
Die finishing back side	CHROMIUM/NICKEL
Die size (micron)	2160 x 1960
Metal levels / materials	2 levels / AlSiCu (1.2 µm last level)
Die finishing front side	SiN / Polyimide
Diffusion Lots #	Lot 1: 6222KTF, Lot 2: 62302LE, Lot 3: 62302LF

Assembly Information	
Assembly plant location	ST Shenzhen (China)
Package description	SO8
Molding compound	SUMITOMO EME-G700KC
Wires bonding materials/diameters	Au 1.0mils
Die attach material	GLUE ABLEBOND 8601S-25
Assembly Lots #	<p>Lot1: 993050PU01(NN), 993050PURR(HH), 993050PURQ(LL), Lot2: 993050Q001(NN), 993050Q0RR(HH), 993050Q0RQ(LL), Lot3: 993050PW01(NN), 993050PWRR(HH), 993050PWRQ(LL),</p> <p>NOTE: the reliability evaluation was done on lots with different assembly configurations both in terms of Bonding Force and Ultra-Sonic Power. 3 lots nominal (NN), 6 lots worst cases (HH: Highest Bonding Force and Highest US Power, LL: Lower Bonding Force and Lower US Power)</p>

Reliability Information	
Reliability test execution location	STM Catania (Italy)

- 3. Devices characteristics

3.1 Generalities

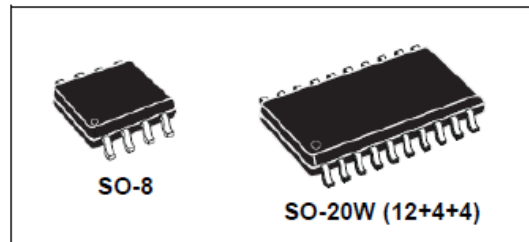


L4949ED-E L4949EP-E

Multifunction very low drop
voltage regulator

Features

- ECOPACK®: lead free and RoHS compliant
- Automotive Grade: compliance with AEC guidelines
- Operating DC supply voltage range 5 V - 28 V
- Transient supply voltage up to 40V
- Extremely low quiescent current in standby mode
- High precision standby output voltage 5V±1%
- Output current capability up to 100mA
- Very low dropout voltage less than 0.5V
- Reset circuit sensing the output voltage
- Programmable reset pulse delay with external capacitor
- Voltage sense comparator
- Thermal shutdown and short circuit protections



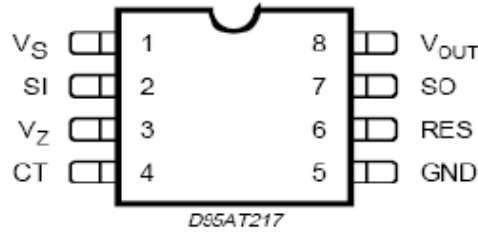
Description

The L4949ED-E and L4949EP-E are monolithic integrated 5V voltage regulators with a very low dropout output and additional functions as power-on reset and input voltage sense. They are designed for supplying the microcomputer controlled systems especially in automotive applications.

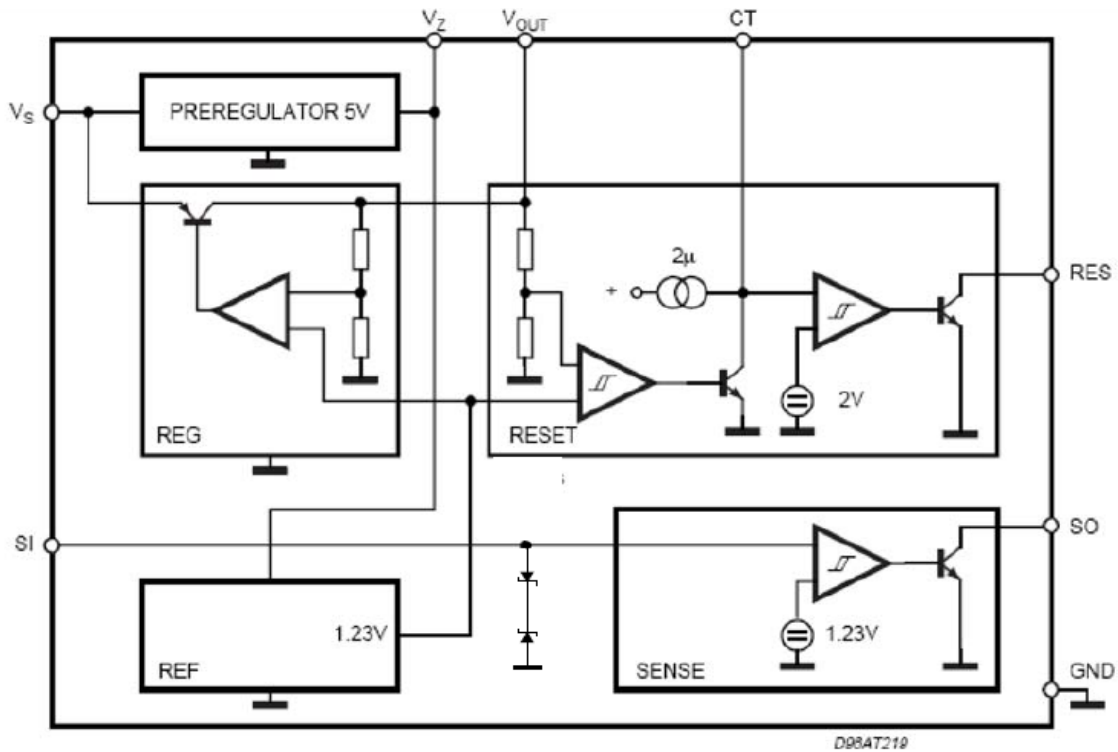
Table 1. Device summary

Package	Order codes	
	Tube	Tape and reel
SO-8	L4949ED-E	L4949EDTR-E
SO-20W	L4949EP-E	L4949EPTR-E

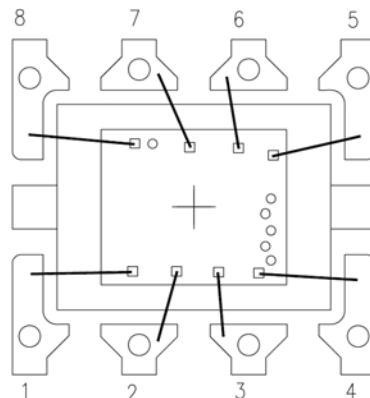
3.2 Pins connection



3.3 Blocks diagram



3.4 Bonding diagram



- 4. Reliability qualification plan and results

Test group A: Accelerated Environment Stress					
AEC #	Test Name	STM Test Conditions	Sample Size/Lots	Results Fails/SS/Lots	Comments
A1	PC Pre Cond	- Preconditioning according to Jecdec JESD22-A113F including 5 Temperature Cycling Ta=-40°C/+60°C - Reflow according to level 3 Jecdec JSTD020D-1 - 100 Temperature Cycling Ta=-50°C/+150°C	Before THB, AC, TC, HTOL		
A2	THB Temp Humidity Bias	Ta=85°C, RH=85%, Vcc=24V for 1000 hours	77/3	0/77/3	
A3	AC Autoclave	ENV. SEQ. Enviromental Sequence TC (Ta=-65°C / +150°C for 100 cycles) + AC (Ta=121°C, Pa=2atm for 96 hours)	77/9	0/77/9	
A4	TC Temp. Cycling	Ta=-65°C / +150°C for 500 cycles	77/9	0/77/9	
A5	PTC Power Temp. Cycling	Ta=-40°C / +125°C for 1000 cycles.	-	-	Not Applicable Pdis<1W
A6	HTSL High Temp. Storage Life	Ta=150°C for 1000 hours.	45/9	0/45/9	

Test group B: Accelerated Lifetime Simulation					
AEC #	Test Name	STM Test Conditions	Sample Size/Lots	Results Fails/SS/Lots	Comments
B1	HTOL High Temp. Op. Life	Bias Dynamic stress (JESD22-A108): Ta=125°C, Vcc=28V for 1000 hours	77/3	0/77/3	
B2	ELFR Early Life Failure Rate	Parts submitted to HTOL per JESD22-A108 requirements; GRADE 1: 24 hours at 150°C	800/3	Passed	
B3	EDR Endurance Data Retention	Only for memory devices	-	-	Not Applicable

Test group C: Package Assembly Integrity					
AEC #	Test Name	STM Test Conditions	Sample Size/Lots	Results Fails/SS/Lots	Comments
C1	WBS Wire Bond Shear	Per AEC-Q100-001	30 bonds /minimum 5 units/1 lot	All measurement within spec limits	
C2	WBP Wire Bond Pull	Per MIL-STD883, M2011 Condition C or D	30 bonds /minimum 5 units/1 lot	All measurement within spec limits	
C3	SD Solderability		15/3	All measurement within spec limits	
C4	PD Physical Dimensions		10/3	All measurement within spec limits	
C5	SBS Solder Ball Shear	Only for BGA package	-	-	Not Applicable
C6	LI Lead Integrity	Not required for Surface Mount Devices	-	-	Not Applicable

Test group D: Die Fabrication Reliability					
AEC #	Test Name	STM Test Conditions	Sample Size/Lots	Results Fails/SS/Lots	Comments
D1	EM Electromigration				Not Applicable for BIPOLAR technology
D2	TDDB Time Dependent Dielectric Breakdown				Not Applicable for BIPOLAR technology
D3	HCI Hot Carrier Injection				Not Applicable for BIPOLAR technology
D4	NBTI Negative Bias Temperature Instability				Not Applicable for BIPOLAR technology
D5	SM Stress Migration				Not Applicable for BIPOLAR technology

Test group E: Electrical Verification					
AEC #	Test Name	STM Test Conditions	Sample Size/ Lots	Results Fails/SS/Lots	Comments
E2	ESD HBM	HBM=[R=1.5kΩ, C=150pF]	1 lot	±2.0kV	
E3	ESD CDM		1 lot	±500V ±750V (<i>Corner pins</i>)	
E4	LU Latch-Up	Injection current : ±100mA Over voltage: 1.5 x Vop max	6/1	Inj-L/Inj-H@125°C: ±100mA all pins Inj+L/Inj+H@125°C: ±100mA all pins OV: passed	
E5	ED Electrical Distributions		30/3	Done	
E7	CHAR Characterization			-	Not Applicable for this qualification
E8	GL Gate Leakage		6/1	PASSED	
E9	EMC Electromagnetic Compatibility		-	-	Not Applicable for this qualification
E10	SC Short Circuit Characterization	According to AEC-Q100-012	-	-	

Test group F: Defects Screening Tests					
AEC #	Test Name	STM Test Conditions	Sample Size/ Lots	Results Fails/SS/Lots	Comments
F1	PAT Process Average Testing		Not performed on qualification lots listed on traceability section of this report. To be implemented starting from first production lot		
F2	SBA Statistical Bin/Yield Analysis				

Test group G: Cavity Package Integrity Tests					
AEC #	Test Name	STM Test Conditions	Sample Size/ Lots	Results Fails/SS/Lots	Comments
G1	MS Mechanical Shock				Not applicable: not for plastic packaged devices
G2	VFV Variable Frequency Vibration				
G3	CA Constant Acceleration				
G4	GFL Gross/Fine Leak				
G5	DROP Package Drop				
G6	LT Lid Torque				
G7	DS Die Shear				
G8	IWV Internal Water Vapor				



Public Products List

PCN Title : W023 Silicon Line housed in SO-8 : Transfer from AMK5 to AMK6 and Assy /Final Test from Muar to Shenzhen

PCN Reference : APG-PTS/14/8309

PCN Created on : 04-FEB-2014

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change:

ST COMMERCIAL PRODUCT

L4949ED-E

L4949EDTR-E

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